

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,897,542 B2
DATED : May 24, 2005
INVENTOR(S) : Charles H. Dennison

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, replace
"6,097,677 A 8/2000 Wu" with -- 6,087,677 A 7/2000 Wu --.

Column 3,

Line 26, replace "nitride (Si_3N) or silicon oxynitride ($\text{Si}_x\text{O}_y\text{N}_z$, wherein x, y" with
-- nitride (Si_3N_4) or silicon oxynitride ($\text{Si}_x\text{O}_y\text{N}_z$, wherein x, y --.

Column 6,

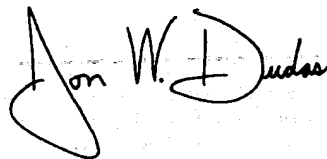
Line 36, replace "through to the first diffusion region and having a second" with
-- through to the first diffusion region and having a second --.

Column 8,

Line 16, replace "with the planar uppermost surface. of the insulative" with
-- with the planar uppermost surface of the insulative --.

Signed and Sealed this

Fourth Day of April, 2006

A handwritten signature in black ink, appearing to read "Jon W. Dudas", is written over a faint, rectangular grid pattern.

JON W. DUDAS
Director of the United States Patent and Trademark Office